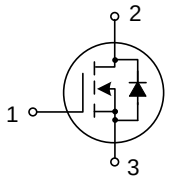
4A, 700V N-CHANNEL MOSFET

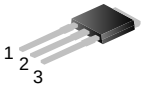
GENERAL DESCRIPTION

SVF4N70MJ is an N-channel enhancement mode power MOS field effect transistor which is produced using Silan proprietary F-Cell™ high-voltage planar VDMOS technology. The improved process and cell structure have been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode.

These devices are widely used in AC-DC power supplies, DC-DC converters and H-bridge PWM motor drivers.



1.Gate 2.Drain 3.Source



TO-251J-3L

FEATURES

- 4A,700V,RDS(on)(typ)=2.5Ω@VGS=10V
- Low gate charge
- Low Crss
- Fast switching
- Improved dv/dt capability

ORDERING INFORMATION

Part No.	Package	Marking	Hazardous Substance Control	Packing Type
SVF4N70MJ	TO-251J-3L	SVF4N70MJ	Halogen free	Tube

ABSOLUTE MAXIMUM RATINGS (T_C=25°C UNLESS OTHERWISE NOTED)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	700	V
Gate-Source Voltage		V_{GS}	±30	V
Drain Current	T_C=25°C	I_D	4.0	A
	T_C=100°C		2.53	
Drain Current Pulsed		I_{DM}	16.0	A
Power Dissipation(T_C=25°C)		P_D	80	W
-Derate above 25°C			0.64	W/°C
Single Pulsed Avalanche Energy (Note 1)		E_{AS}	242	mJ
Operation Junction Temperature Range		T_{stg}	-55～+150	°C
Storage Temperature Range		I_{DM}	-55～+150	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.56	°C/W
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	62.0	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C UNLESS OTHERWISE NOTED)

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain -Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V, I_D=250μA	700	--	--	V
Drain-Source Leakage Current	I_{DSS}	V_{DS}=700V, V_{GS}=0V	--	--	1.0	μA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±30V, V_{DS}=0V	--	--	±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS}= V_{DS}, I_D=250μA	2.0	--	4.0	V
Static Drain- Source On State Resistance	$R_{DS(on)}$	V_{GS}=10V, I_D=2.0A	--	2.5	3.0	Ω
Input Capacitance	C_{iss}	V_{DS}=25V, V_{GS}=0V, f=1.0MHz	--	570.00	--	pF
Output Capacitance	C_{oss}		--	58.30	--	
Reverse Transfer Capacitance	C_{rss}		--	2.91	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=350V, R_G=25Ω, I_D=4.0A (Note2, 3)	--	15.87	--	ns
Turn-on Rise Time	t_r		--	28.60	--	
Turn-off Delay Time	$t_{d(off)}$		--	39.07	--	
Turn-off Fall Time	t_f		--	29.60	--	
Total Gate Charge	Q_g	V_{DS}=560V, I_D=4.0A, V_{GS}=10V (Note 2, 3)	--	13.33	--	nC
Gate-Source Charge	Q_{gs}		--	3.58	--	
Gate-Drain Charge	Q_{gd}		--	5.76	--	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Continuous Source Current	I_S	Integral Reverse P-N Junction Diode in the MOSFET	--	--	4.0	A
Pulsed Source Current	I_{SM}		--	--	16.0	
Diode Forward Voltage	V_{SD}	I_S=4.0A,V_{GS}=0V	--	--	1.4	V
Reverse Recovery Time	T_{rr}	I_S=4.0A,V_{GS}=0V, dI_F/dt=100A/μS	--	437.0	--	ns
Reverse Recovery Charge	Q_{rr}		--	2.2	--	μC

Notes:

1. L=30mH, I_{AS}=3.72A, V_{DD}=100V, R_G=25Ω, starting T_J=25°C;
2. Pulse Test: Pulse width ≤300μs,Duty cycle≤2%;
3. Essentially independent of operating temperature.

TYPICAL CHARACTERISTICS

Figure 1. On-Region Characteristics

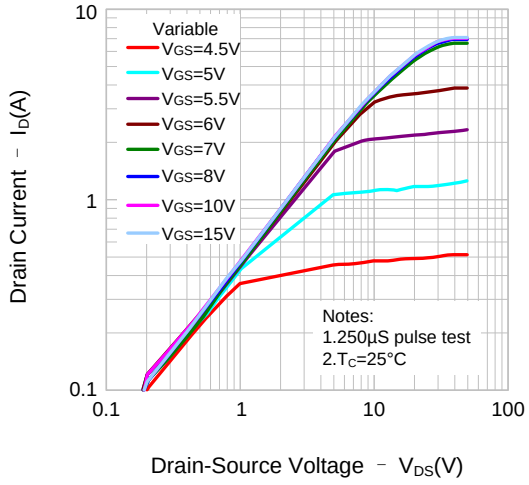


Figure 2. Transfer Characteristics

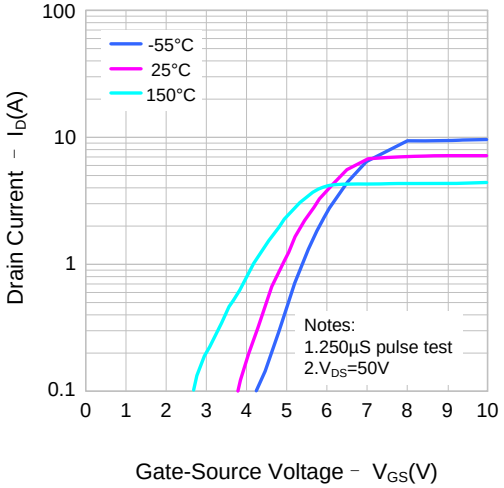


Figure 3. On-Resitance Variation vs. Drain Current and Gate Voltage

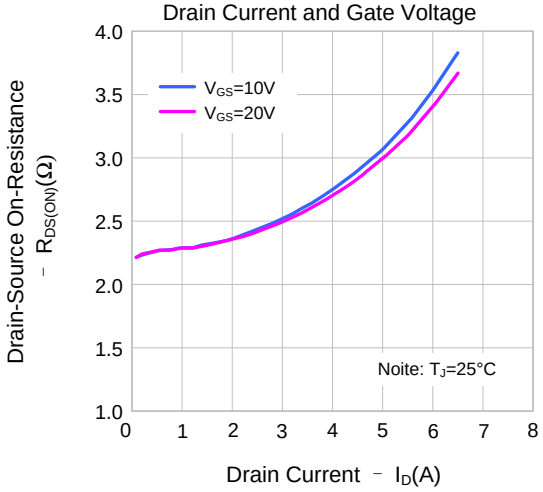
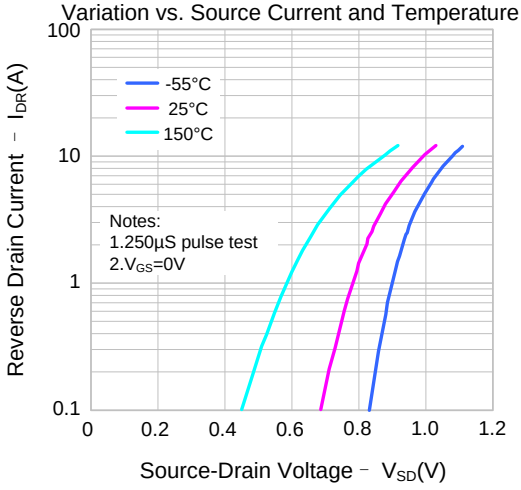


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature



TYPICAL CHARACTERISTICS(CONTINUED)

Figure 5. Capacitance Characteristics

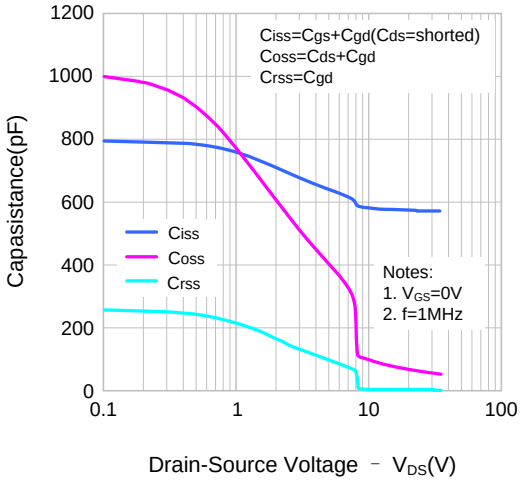


Figure 6. Gate Charge Characteristics

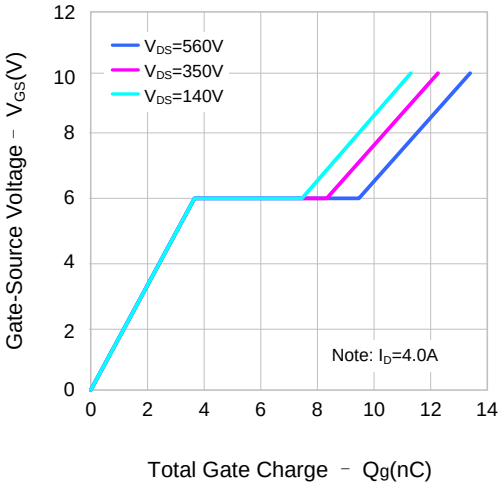


Figure 7. Breakdown Voltage Variation vs. Temperature

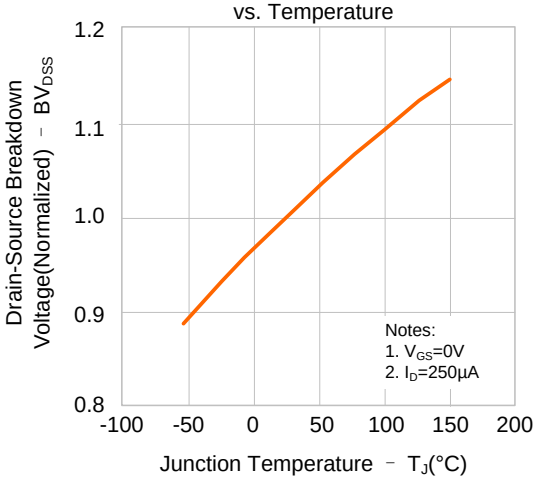


Figure 8. On-resistance Variation vs. Temperature

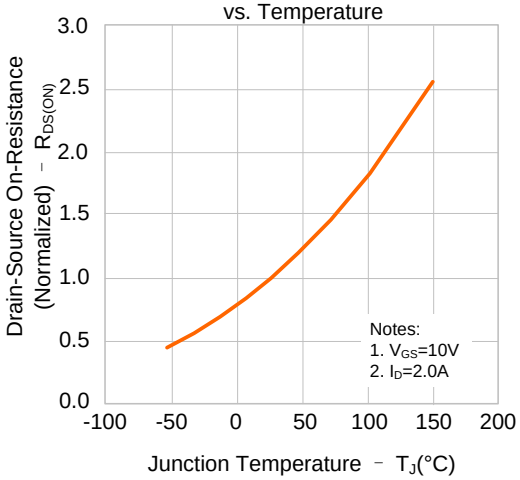


Figure 9. Max. Safe Operating Area

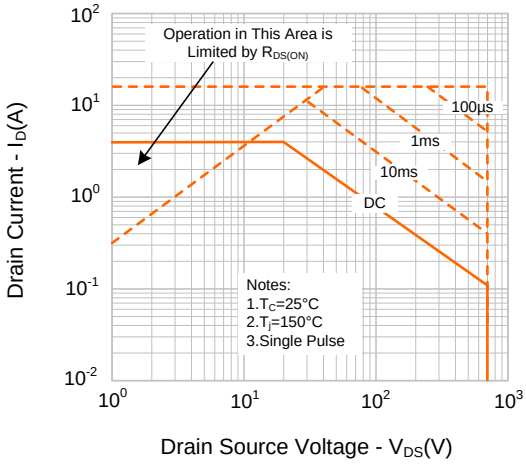
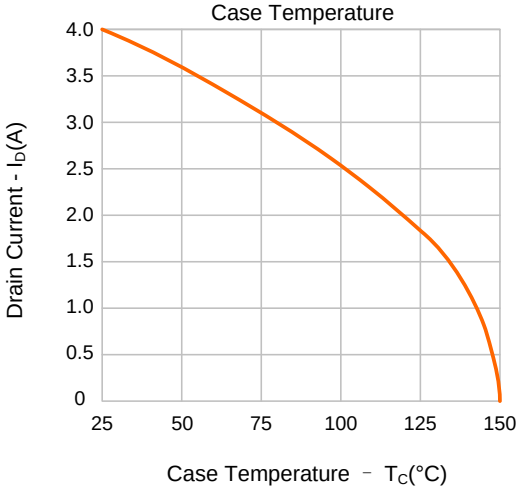
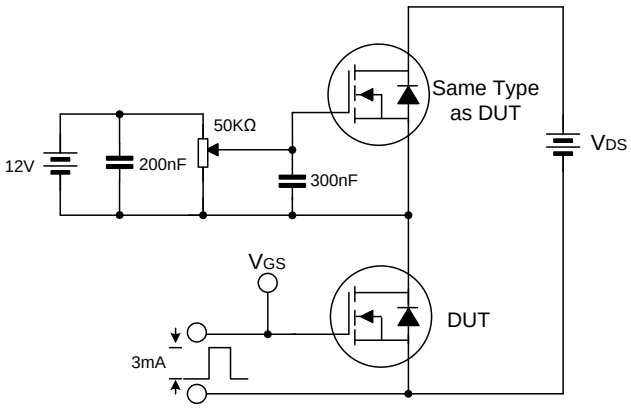


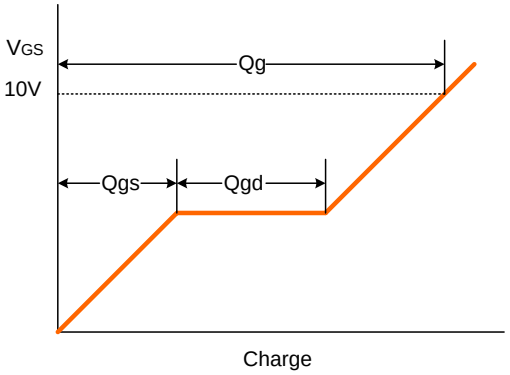
Figure 10. Maximum Drain Current vs. Case Temperature



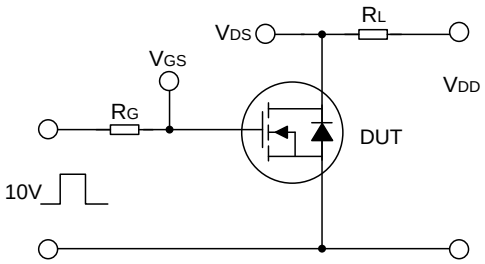
TYPICAL TEST CIRCUIT

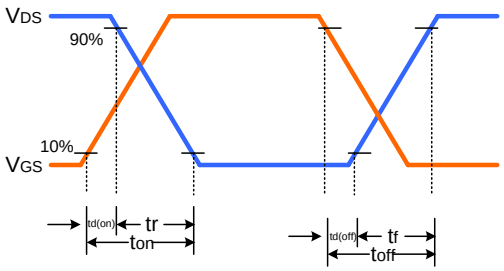
Gate Charge Test Circuit & Waveform



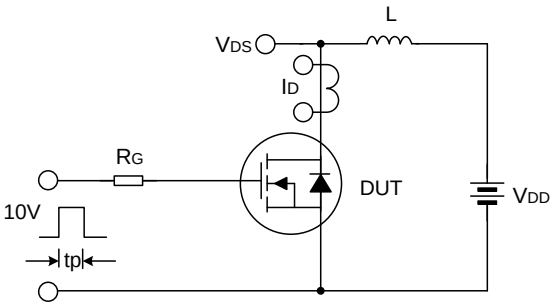


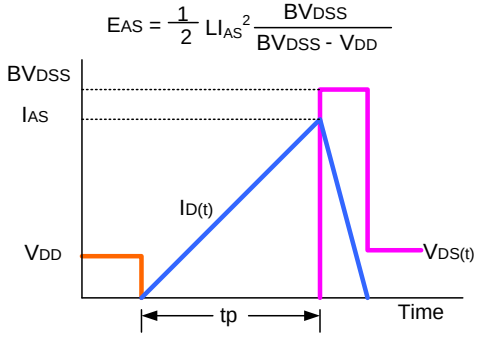
Resistive Switching Test Circuit & Waveform





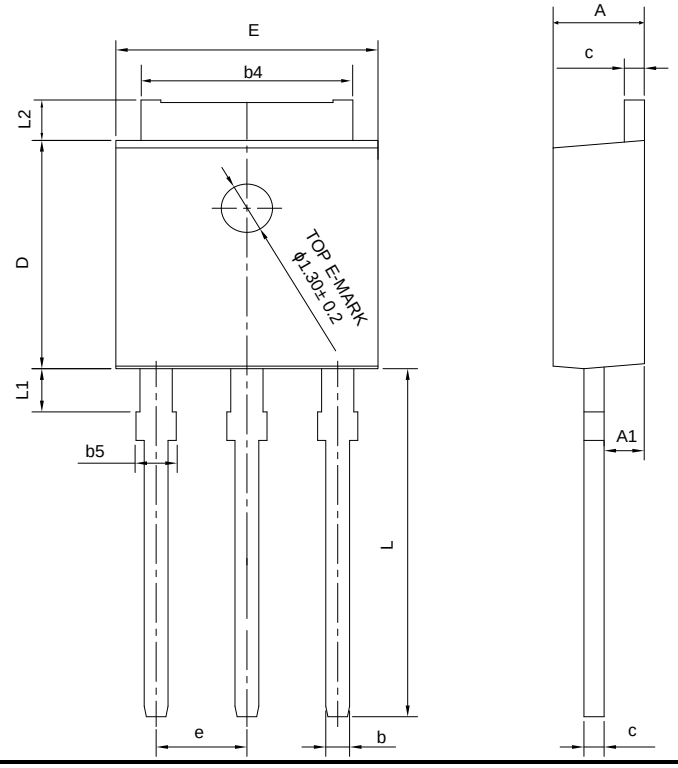
Unclamped Inductive Switching Test Circuit & Waveform





PACKAGE OUTLINE

TO-251J-3L **Unit：mm**



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	2.18	2.30	2.39
A1	0.89	1.00	1.14
b	0.56	—	0.89
b4	4.95	5.33	5.46
b5	—	—	1.05
c	0.46	—	0.61
D	5.97	6.10	6.27
E	6.35	6.60	6.73
e	2.29 BCS		
L	8.89	9.30	9.65
L1	0.95	—	1.50
L2	0.89	—	1.27

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Rev.: 1.7

Revision History:

1. Deleted NOMENCLATURE
2. Modify Important notice

Rev.: 1.6

Revision History:

1. Update the package outline of TO-251J-3L

Rev.: 1.5

Revision History:

1. Modify the value of $R_{DS(on)}$， update Figure SOA

Rev.: 1.4

Revision History:

1. Modify the thermal characteristics

Rev.: 1.3

Revision History:

1. Modify the ordering information

Rev.: 1.2

Revision History:

1. Change the schematic diagram of MOS

Rev.: 1.1

Revision History:

1. Modify “ORDERING INFORMATION”

Rev.: 1.0

Revision History:

1. Initial release